
 STATUTORY INSTRUMENTS

1981 No. 668

CUSTOMS AND EXCISE

The Export of Goods (Control) (Amendment) Order 1981

Made - - - - 28th April 1981

Coming into Operation 14th May 1981

The Secretary of State, in exercise of the powers conferred by section 1 of the Import, Export and Customs Powers (Defence) Act 1939(a) and now vested in him(b), and of all other powers enabling him in that behalf, hereby makes the following Order:—

1. This Order may be cited as the Export of Goods (Control) (Amendment) Order 1981 and shall come into operation on 14th May 1981.

2. Group 3I of Part II of Schedule 1 to the Export of Goods (Control) Order 1978(c) shall be amended by deleting the entry relating to monocrystalline compounds and metallic materials and adding after the entry relating to composite structures and laminates the following—

“Compounds and materials, the following—

- (1) Monocrystalline silicon having any of the following characteristics:—... .. A
- (a) containing bismuth, indium, gallium, selenium or thallium at an average carrier concentration of greater than 10^{16} per cubic centimetre;
- (b) containing arsenic at an average carrier concentration of greater than 10^{16} per cubic centimetre and less than 10^{18} per cubic centimetre;
- (c) having P-type conductivity and a resistivity of 5,000 ohm.cm or greater; or
- (d) in the form of wafers (slices) or ingots (boules), having
for all N-type a resistivity of 50 ohm.cm or less;
for P-type 1-1-1 a resistivity of 50 ohm.cm or less;
for P-type 1-0-0 a resistivity of 100 ohm.cm or less;
- (2) Monocrystalline gallium compounds A
except—
- (a) gallium phosphide and
- (b) gallium arsenide, gallium arsenide phosphide and gallium nitride, having all of the following characteristics:—

(a) 1939 c. 69.

(b) See S.I. 1970/1537.

(c) S.I. 1978/796, to which there are amendments not relevant to this Order.

- (i) diffusion processed wafers;
(ii) selenium, tellurium, silicon, sulphur, tin or zinc doped;
(iii) dislocation density (EPD) greater than 10,000 per square centimetre;
(iv) carrier concentration greater than 10^{16} per cubic centimetre; and
(v) carrier mobility less than 2,000 square centimetres per volt second;
- (3) Monocrystalline indium compounds in any form C
(4) Composites (hetero-epitaxial materials) consisting of a monocrystalline insulating substrate epitaxially layered with silicon, compounds of gallium or compounds of indium C
(5) Mercury cadmium telluride compounds in any form A
(6) Electronic grade polycrystalline silicon having a maximum concentration of P-type impurity (e.g. boron) of 0.3 parts in 10^9 or a maximum concentration of N-type impurity (e.g. phosphorus) of 1.5 parts in 10^9 , or both. Purity shall be verified according to ASTM specification F 574-78 or equivalent followed by resistivity measurement according to ASTM specification F 43-78 or equivalent A''

A. C. G. Lowry,
An Assistant Secretary,
Department of Trade.

28th April 1981.

EXPLANATORY NOTE

(This Note is not part of the Order.)

This Order amends the Export of Goods (Control) Order 1978 by substituting a new item for the item relating to monocrystalline compounds and metallic materials in Group 3I of Part II of Schedule 1 to the Order. Apart from re-defining goods already subject to export control, the Order extends control to silicon ingots (boules) and to mercury cadmium telluride compounds in any form. It extends control on most of the goods concerned to all destinations. It also removes control on certain tin-doped gallium compounds.

THE UNIVERSITY OF CHICAGO PRESS

SI 1981/668
ISBN 0-11-016668-X



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